

Data Sheet

August 1999

File Number 4772

80V/2.5A Peak, High Frequency Full Bridge FET Driver

The HCA10008 is a high frequency, medium voltage Full Bridge N-Channel FET driver IC, available in 20 lead plastic SOIC package. The HCA10008 can drive every possible switch combination except those which would cause a shoot through condition. The HCA10008 can switch at frequencies up to 1MHz and is well suited to driving Voice Coil Motors, high-frequency Class D audio amplifiers, and power supplies.

For example, the HCA10008 can drive medium voltage brush motors, and two HCA10008s can be used to drive high performance stepper motors, since the short minimum "on-time" can provide fine micro-stepping capability.

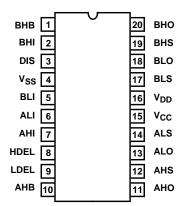
Short propagation delays of approximately 55ns maximizes control loop crossover frequencies and dead-times which can be adjusted to near zero to minimize distortion, resulting in rapid, precise control of the driven load.

Ordering Information

PART NUMBER	TEMP RANGE (°C)	PACKAGE	PKG. NO.	
HCA10008	-40 to 85	20 Ld SOIC (W)	M20.3	

Pinout

HCA10008 (SOIC) TOP VIEW



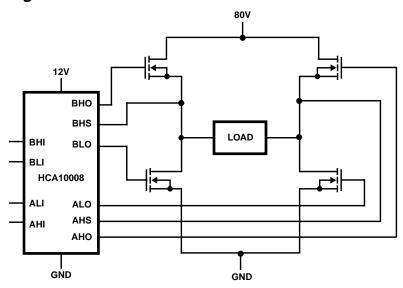
Features

- Independently Drives 4 N-Channel FET in Half Bridge or Full Bridge Configurations
- Bootstrap Supply Max Voltage to 95V_{DC}
- Drives 1000pF Load at 1MHz in Free Air at 50°C with Rise and Fall Times of Typically 10ns
- User Programmable Dead Time
- On-Chip Charge Pump and Bootstrap Upper Bias Supplies
- DIS (Disable) Overrides Input Control
- Input Logic Thresholds Compatible with 5V to 15V Logic Levels
- Very Low Power Consumption
- · Undervoltage Protection

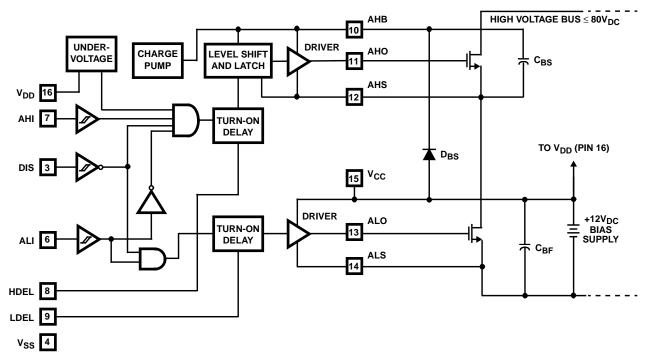
Applications

- Medium/Large Voice Coil Motors
- Full Bridge Power Supplies
- · Class D Audio Power Amplifiers
- · High Performance Motor Controls
- · Noise Cancellation Systems
- · Battery Powered Vehicles
- Peripherals
- U.P.S.
- Related Literature
 - AN9405 Application Note for the HIP4081A and the HCA10008

Application Block Diagram



Functional Block Diagram (1/2 HCA10008)

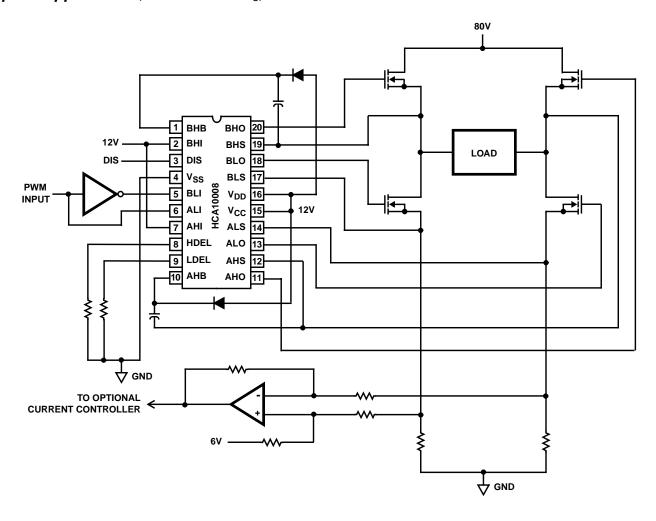


TRUTH TABLE

	INF	OUTPUT			
ALI, BLI	AHI, BHI	U/V	DIS	ALO, BLO	АНО, ВНО
Х	Х	Х	1	0	0
1	Х	0	0	1	0
0	1	0	0	0	1
0	0	0	0	0	0
Х	Х	1	Х	0	0

NOTE: X signifies that input can be either a "1" or "0".

Typical Application (PWM Mode Switching)



HCA10008

Pin Descriptions

PIN NUMBER	SYMBOL	DESCRIPTION
1	ВНВ	B High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin. Internal charge pump supplies 30μA out of this pin to maintain bootstrap supply. Internal circuitry clamps the bootstrap supply to approximately 12.8V.
2	ВНІ	B High-side Input. Logic level input that controls BHO driver (Pin 20). BLI (Pin 5) high level input overrides BHI high level input to prevent half-bridge shoot-through, see Truth Table. DIS (Pin 3) high level input overrides BHI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}). An internal 100 μ A pull-up to V_{DD} will hold BHI high, so no connection is required if high-side and low-side outputs are to be controlled by the low-side input
3	DIS	DISable input. Logic level input that when taken high sets all four outputs low. DIS high overrides all other inputs. When DIS is taken low the outputs are controlled by the other inputs. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}). An internal 100 μ A pull-up to V_{DD} will hold DIS high if this pin is not driven.
4	V _{SS}	Chip negative supply, generally will be ground.
5	BLI	B Low-side Input. Logic level input that controls BLO driver (Pin 18). If BHI (Pin 2) is driven high or not connected externally then BLI controls both BLO and BHO drivers, with dead time set by delay currents at HDEL and LDEL (Pin 8 and 9). DIS (Pin 3) high level input overrides BLI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V _{DD}). An internal 100µA pull-up to V _{DD} will hold BLI high if this pin is not driven.
6	ALI	A Low-side Input. Logic level input that controls ALO driver (Pin 13). If AHI (Pin 7) is driven high or not connected externally then ALI controls both ALO and AHO drivers, with dead time set by delay currents at HDEL and LDEL (Pin 8 and 9). DIS (Pin 3) high level input overrides ALI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V _{DD}). An internal 100µA pull-up to V _{DD} will hold ALI high if this pin is not driven.
7	AHI	A High-side Input. Logic level input that controls AHO driver (Pin 11). ALI (Pin 6) high level input overrides AHI high level input to prevent half-bridge shoot-through, see Truth Table. DIS (Pin 3) high level input overrides AHI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}). An internal 100 μ A pull-up to V_{DD} will hold AHI high, so no connection is required if high-side and low-side outputs are to be controlled by the low-side input
8	HDEL	High-side turn-on DELay. Connect resistor from this pin to V_{SS} to set timing current that defines the turn-on delay of both high-side drivers. The low-side drivers turn-off with no adjustable delay, so the HDEL resistor guarantees no shoot-through by delaying the turn-on of the high-side drivers. HDEL reference voltage is approximately 5.1V.
9	LDEL	Low-side turn-on DELay. Connect resistor from this pin to V _{SS} to set timing current that defines the turn-on delay of both low-side drivers. The high-side drivers turn-off with no adjustable delay, so the LDEL resistor guarantees no shoot-through by delaying the turn-on of the low-side drivers. LDEL reference voltage is approximately 5.1V.
10	AHB	A High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin. Internal charge pump supplies 30μA out of this pin to maintain bootstrap supply. Internal circuitry clamps the bootstrap supply to approximately 12.8V.
11	AHO	A High-side Output. Connect to gate of A High-side power MOSFET.
12	AHS	A High-side Source connection. Connect to source of A High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
13	ALO	A Low-side Output. Connect to gate of A Low-side power MOSFET.
14	ALS	A Low-side Source connection. Connect to source of A Low-side power MOSFET.
15	V _{CC}	Positive supply to gate drivers. Must be same potential as V _{DD} (Pin 16). Connect to anodes of two bootstrap diodes
16	V _{DD}	Positive supply to lower gate drivers. Must be same potential as V _{CC} (Pin 15). Decouple this pin to V _{SS} (Pin 4).
17	BLS	B Low-side Source connection. Connect to source of B Low-side power MOSFET.
18	BLO	B Low-side Output. Connect to gate of B Low-side power MOSFET.
19	BHS	B High-side Source connection. Connect to source of B High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
20	вно	B High-side Output. Connect to gate of B High-side power MOSFET.

Absolute Maximum Ratings

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)
SOIC Package	85
Maximum Storage Temperature Range65	^o C to 150 ^o C
Maximum Junction Temperature	125 ^o C
Maximum Lead Temperature (Soldering 10s))	300°C
(SOIC - Lead Tips Only)	

Operating Conditions

Supply Voltage, V $_{DD}$ and V $_{CC}$... +9.5V to +15V Voltage on ALS, BLS ... -1.0V to +1.0V Voltage on AHB, BHB ... V $_{AHS}$, BHS +5V to V $_{AHS}$, BHS +15V Input Current, HDEL and LDEL ... -500 μ A to -50 μ A Ambient Temperature Range ... -40 $^{\circ}$ C to 85 $^{\circ}$ C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = V_{BHS} = 0V$, $V_{BHS} = V_{BHS} = 100$ K and $V_{AHS} = 100$ K and V_{AHS}

				T _J = 25°C			T _{JS} =-40°CTO 125°C	
PARAMETER	SYMBOL	TEST CONDITIONS	MIN TYP MAX		MIN MAX		UNITS	
SUPPLY CURRENTS AND CHAP	RGE PUMPS		'	•				
V _{DD} Quiescent Current	I _{DD}	All inputs = 0V	8.5	10.5	14.5	7.5	14.5	mA
V _{DD} Operating Current	I _{DDO}	Outputs switching f = 500kHz	9.5	12.5	15.5	8.5	15.5	mA
V _{CC} Quiescent Current	Icc	All Inputs = 0V, I _{ALO} = I _{BLO} = 0	-	0.1	10	-	20	μА
V _{CC} Operating Current	Icco	f = 500kHz, No Load	1	1.25	2.0	0.8	3	mA
AHB, BHB Quiescent Current Qpump Output Current	I _{AHB} , I _{BHB}	All Inputs = 0V, $I_{AHO} = I_{BHO} = 0$ $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 10V$	-50	-30	-11	-60	-10	μА
AHB, BHB Operating Current	I _{AHBO} , I _{BHBO}	f = 500kHz, No Load	0.6	1.2	1.5	0.5	1.9	mA
AHS, BHS, AHB, BHB Leakage Current	I _{HLK}	V _{BHS} = V _{AHS} = 80V, V _{AHB} = V _{BHB} = 93V	-	0.02	1.0	-	10	μА
AHB-AHS, BHB-BHS Qpump Output Voltage	V _{AHB} -V _{AHS} V _{BHB} -V _{BHS}	I _{AHB} = I _{AHB} = 0, No Load	11.5	12.6	14.0	10.5	14.5	V
INPUT PINS: ALI, BLI, AHI, BHI,	AND DIS							
Low Level Input Voltage	V _{IL}	Full Operating Conditions	-	-	1.0	-	0.8	V
High Level Input Voltage	V _{IH}	Full Operating Conditions	2.5	-	-	2.7	-	V
Input Voltage Hysteresis			-	35	-	-	-	mV
Low Level Input Current	I _{IL}	V _{IN} = 0V, Full Operating Conditions	-130	-100	-75	-135	-65	μΑ
High Level Input Current	l _{IH}	V _{IN} = 5V, Full Operating Conditions	-1	-	+1	-10	+10	μА
TURN-ON DELAY PINS: LDEL A	ND HDEL				•	•	•	
LDEL, HDEL Voltage	V _{HDEL} , V _{LDEL}	$I_{HDEL} = I_{LDEL} = -100\mu A$	4.9	5.1	5.3	4.8	5.4	V

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			T _J = 25 ^o C		T _{JS} = -40°C TO 125°C				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN TYP MAX		MAX	MIN	MAX	AX UNITS	
GATE DRIVER OUTPUT PINS: A	GATE DRIVER OUTPUT PINS: ALO, BLO, AHO, AND BHO								
Low Level Output Voltage	V _{OL}	I _{OUT} = 100mA	0.7	0.85	1.0	0.5	1.1	V	
High Level Output Voltage	V _{CC} -V _{OH}	I _{OUT} = -100mA	0.8	0.95	1.1	0.5	1.2	V	
Peak Pullup Current	l _O +	V _{OUT} = 0V	1.7	2.6	3.8	1.4	4.1	Α	
Peak Pulldown Current	I _O -	V _{OUT} = 12V	1.7	2.4	3.3	1.3	3.6	Α	
Undervoltage, Rising Threshold	UV+		8.1	8.8	9.4	8.0	9.5	V	
Undervoltage, Falling Threshold	UV-		7.6	8.3	8.9	7.5	9.0	V	
Undervoltage, Hysteresis	HYS		0.25	0.4	0.65	0.2	0.7	V	

		T _J = 25°C			T _{JS} = -40°C TO 125°C			
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN	MAX	UNITS
Lower Turn-Off Propagation Delay (ALI-ALO, BLI-BLO)	T _{LPHL}		-	30	60	-	80	ns
Upper Turn-Off Propagation Delay (AHI-AHO, BHI-BHO)	T _{HPHL}		-	35	70	-	90	ns
Lower Turn-On Propagation Delay (ALI-ALO, BLI-BLO)	T _{LPLH}	R _{HDEL} = R _{LDEL} = 10K	-	45	70	-	90	ns
Upper Turn-On Propagation Delay (AHI-AHO, BHI-BHO)	T _{HPLH}	R _{HDEL} = R _{LDEL} = 10K	-	60	90	-	110	ns
Rise Time	T _R		-	10	25	-	35	ns
Fall Time	T _F		-	10	25	-	35	ns
Turn-On Input Pulse Width	T _{PWIN-ON}	R _{HDEL} = R _{LDEL} = 10K	50	-	-	50	-	ns
Turn-Off Input Pulse Width	T _{PWIN-OFF}	R _{HDEL} = R _{LDEL} = 10K	40	-	-	40	-	ns
Turn-On Output Pulse Width	T _{PWOUT-ON}	R _{HDEL} = R _{LDEL} = 10K	40	-	-	40	-	ns
Turn-Off Output Pulse Width	T _{PWOUT-OFF}	R _{HDEL} = R _{LDEL} = 10K	30	-	-	30	-	ns
Disable Turn-Off Propagation Delay (DIS - Lower Outputs)	T _{DISLOW}		-	45	75	-	95	ns
Disable Turn-Off Propagation Delay (DIS - Upper Outputs)	T _{DISHIGH}		-	55	85	-	105	ns
Disable to Lower Turn-On Propagation Delay (DIS - ALO and BLO)	T _{DLPLH}		-	40	70	-	90	ns
Refresh Pulse Width (ALO and BLO)	T _{REF-PW}		240	410	550	200	600	ns
Disable to Upper Enable (DIS - AHO and BHO)	T _{UEN}		-	450	620	-	690	ns

Timing Diagrams

X = A OR B, A AND B HALVES OF BRIDGE CONTROLLER ARE INDEPENDENT

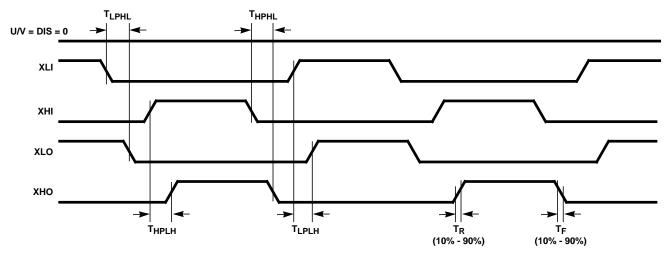
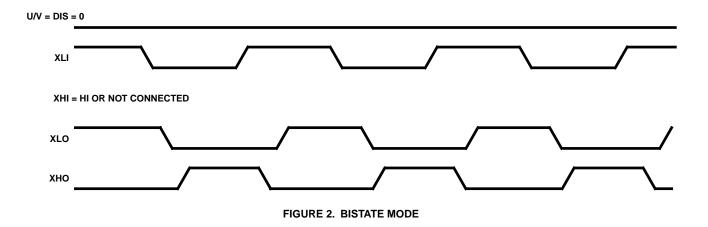


FIGURE 1. INDEPENDENT MODE



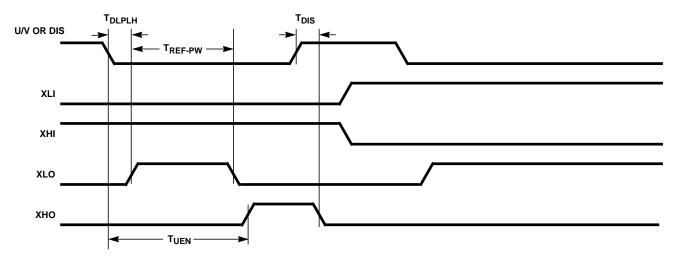


FIGURE 3. DISABLE FUNCTION

Typical Performance Curves $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = 0V$, $V_{BHS} = 0V$, V_{BH

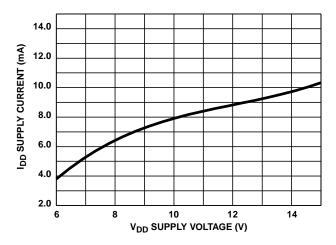


FIGURE 4. QUIESCENT I_{DD} SUPPLY CURRENT vs V_{DD} SUPPLY VOLTAGE

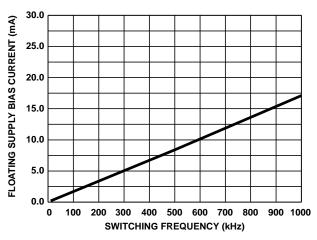


FIGURE 6. SIDE A, B FLOATING SUPPLY BIAS CURRENT vs FREQUENCY (LOAD = 1000pF)

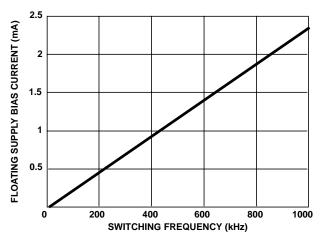


FIGURE 8. I_{AHB}, I_{BHB}, NO-LOAD FLOATING SUPPLY BIAS CURRENT vs FREQUENCY

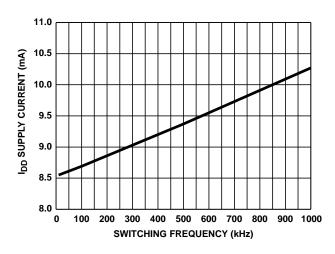


FIGURE 5. I_{DDO} , NO-LOAD I_{DD} SUPPLY CURRENT vs FREQUENCY (kHz)

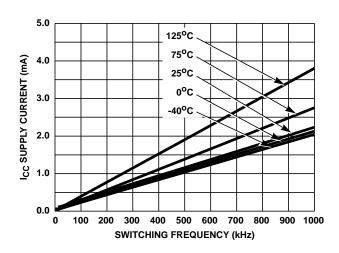


FIGURE 7. I_{CCO} , NO-LOAD I_{CC} SUPPLY CURRENT vs FREQUENCY (kHz) TEMPERATURE

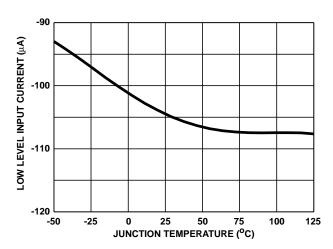


FIGURE 9. ALI, BLI, AHI, BHI LOW LEVEL INPUT CURRENT $I_{\rm IL}$ vs TEMPERATURE

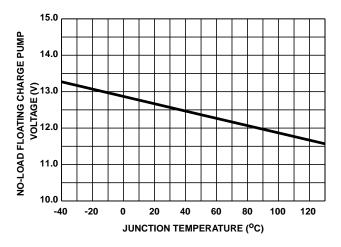


FIGURE 10. AHB - AHS, BHB - BHS NO-LOAD CHARGE PUMP VOLTAGE vs TEMPERATURE

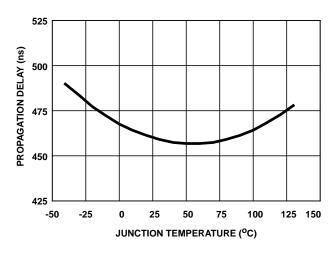


FIGURE 12. DISABLE TO UPPER ENABLE, T_{UEN},
PROPAGATION DELAY vs TEMPERATURE

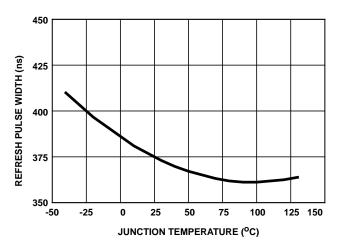


FIGURE 14. T_{REF-PW} REFRESH PULSE WIDTH vs TEMPERATURE

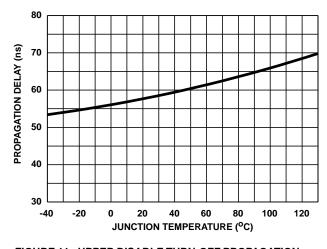


FIGURE 11. UPPER DISABLE TURN-OFF PROPAGATION DELAY T_{DISHIGH} vs TEMPERATURE

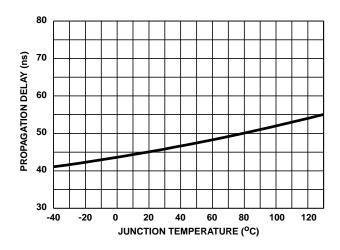


FIGURE 13. LOWER DISABLE TURN-OFF PROPAGATION DELAY T_{DISLOW} vs TEMPERATURE

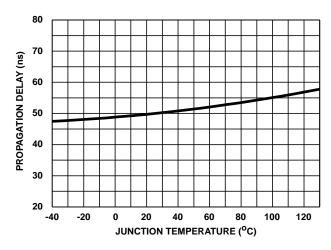


FIGURE 15. DISABLE TO LOWER ENABLE T_{DLPLH}
PROPAGATION DELAY vs TEMPERATURE

Typical Performance Curves $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = 0V$, $V_{BHS} = 0V$, V_{BH

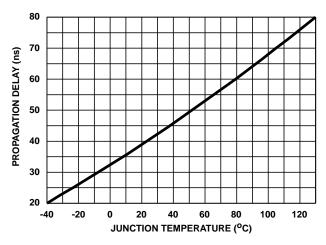


FIGURE 16. UPPER TURN-OFF PROPAGATION DELAY THPHL vs TEMPERATURE

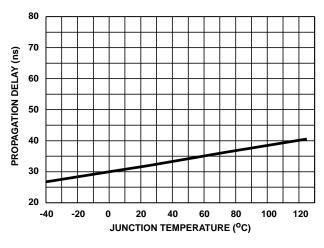


FIGURE 18. LOWER TURN-OFF PROPAGATION DELAY T_{LPHL} vs TEMPERATURE

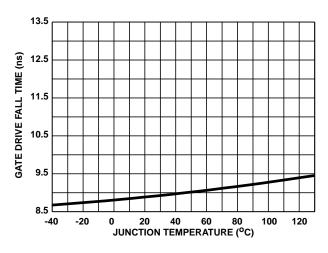


FIGURE 20. GATE DRIVE FALL TIME T_{F} vs TEMPERATURE

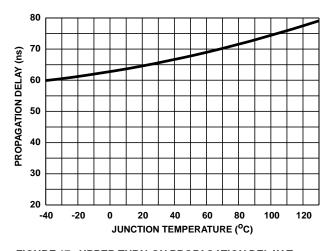


FIGURE 17. UPPER TURN-ON PROPAGATION DELAY THPLH vs TEMPERATURE

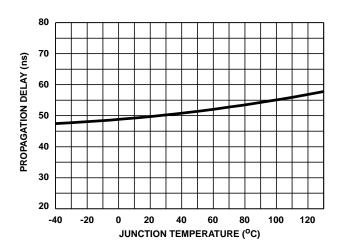


FIGURE 19. LOWER TURN-ON PROPAGATION DELAY T_{LPLH} vs TEMPERATURE

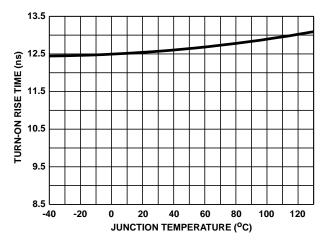


FIGURE 21. GATE DRIVE RISE TIME T_R vs TEMPERATURE

Typical Performance Curves $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BHS} = V_{BHS} = 0V$, $V_{BHS} = 0V$, V_{BHS}

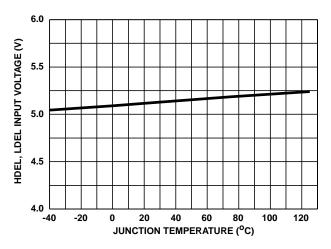


FIGURE 22. V_{LDEL} , V_{HDEL} VOLTAGE vs TEMPERATURE

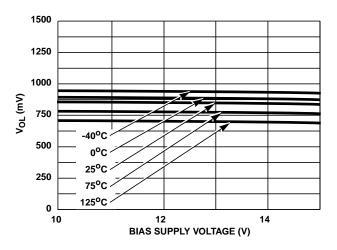


FIGURE 24. LOW LEVEL OUTPUT VOLTAGE V_{OL} vs BIAS SUPPLY AND TEMPERATURE AT 100mA

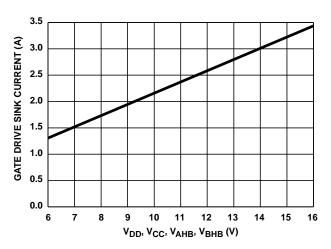


FIGURE 26. PEAK PULLUP CURRENT I_{O+} vs BIAS SUPPLY VOLTAGE

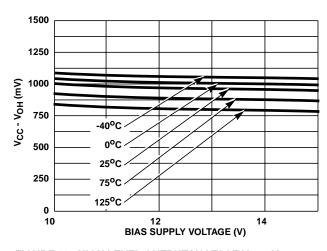


FIGURE 23. HIGH LEVEL OUTPUT VOLTAGE V_{CC} - V_{OH} vs BIAS SUPPLY AND TEMPERATURE AT 100mA

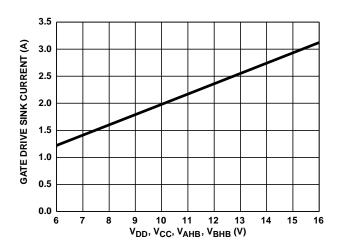


FIGURE 25. PEAK PULLDOWN CURRENT I $_{\rm O}$ vs BIAS SUPPLY VOLTAGE

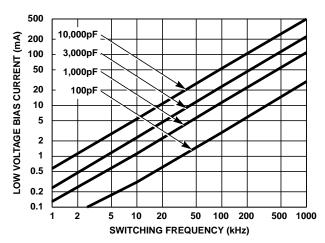
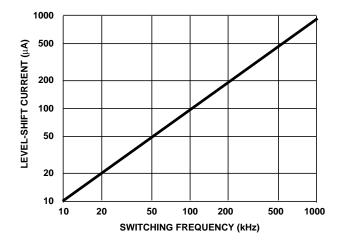


FIGURE 27. LOW VOLTAGE BIAS CURRENT I_{DD} (LESS QUIESCENT COMPONENT) vs FREQUENCY AND GATE LOAD CAPACITANCE

Typical Performance Curves $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = 0V$, $V_{BHS} = 0V$, V_{BH



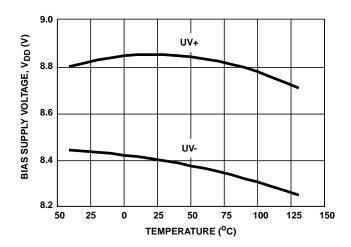


FIGURE 28. HIGH VOLTAGE LEVEL-SHIFT CURRENT vs FREQUENCY AND BUS VOLTAGE

FIGURE 29. UNDERVOLTAGE LOCKOUT vs TEMPERATURE

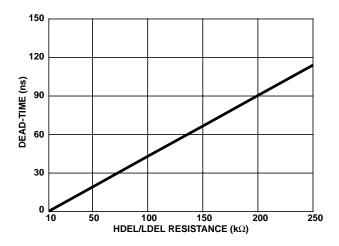
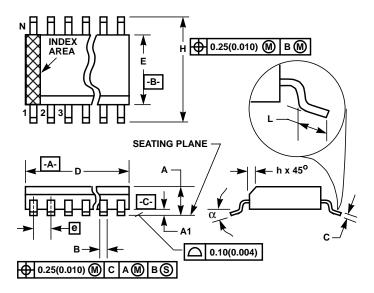


FIGURE 30. MINIMUM DEAD-TIME vs DEL RESISTANCE

Small Outline Plastic Packages (SOIC)



NOTES:

- Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
- 4. Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
- 5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
- 6. "L" is the length of terminal for soldering to a substrate.
- 7. "N" is the number of terminal positions.
- 8. Terminal numbers are shown for reference only.
- The lead width "B", as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch)
- Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

M20.3 (JEDEC MS-013-AC ISSUE C)
20 LEAD WIDE BODY SMALL OUTLINE PLASTIC PACKAGE

	INC	HES	MILLIN		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
А	0.0926	0.1043	2.35	2.65	-
A1	0.0040	0.0118	0.10	0.30	-
В	0.013	0.0200	0.33	0.51	9
С	0.0091	0.0125	0.23	0.32	-
D	0.4961	0.5118	12.60	13.00	3
Е	0.2914	0.2992	7.40	7.60	4
е	0.050	BSC	1.27	BSC	-
Н	0.394	0.419	10.00	10.65	-
h	0.010	0.029	0.25	0.75	5
L	0.016	0.050	0.40	1.27	6
N	2	20		20	7
α	0°	8 ⁰	0°	8°	-

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